SUBSTRATE PROCESSING METHOD, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, PROGRAM AND SUBSTRATE PROCESSING APPARATUS

[ABSTRACT]

It is possible to suppress an adhesion of foreign matters (or particles) to a substrate. There is provided a technique that includes: (a) performing: (a1) supplying a process gas to a substrate arranged in a process chamber through a supplier; and (a2) exhausting a gas in the process chamber through a main exhaust path configured to connect the process chamber to an exhaust apparatus; and (b) exhausting a predetermined gas in the supplier through a subsidiary exhaust path configured to connect the supplier to the main exhaust path without passing through the process chamber, while suppressing or blocking a gas flow from the main exhaust path to the process chamber.

Figure 2A